PMT760EN

100 V N-channel Trench MOSFET

25 October 2012 — Product data sheet

1. Product profile

1.1 General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT223 (SC-73) small Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Logic-level compatible
- Very fast switching
- Trench MOSFET technology

1.3 Applications

- Relay driver
- LED backlight driver
- Low-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage	T_j = 25 °C		-	-	100	V
V_{GS}	gate-source voltage			-20	-	20	V
I_D	drain current	V_{GS} = 10 V; T_{amb} = 25 °C; t ≤ 5 s	[1]	-	-	1.3	A
Static characteristics							
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 0.8 A; T_j = 25 °C		-	760	950	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm^2.

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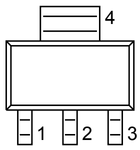
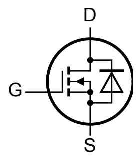
2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 SC-73 (SOT223)	 017aaa253
2	D	drain		
3	S	source		
4	D	drain		

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMT760EN	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223

4. Marking

Table 4. Marking codes

Type number	Marking code
PMT760EN	T760EN

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T_j = 25 °C		-	100	V
V_{GS}	gate-source voltage			-20	20	V
I_D	drain current	V_{GS} = 10 V; T_{amb} = 25 °C; t ≤ 5 s	[1]	-	1.3	A
		V_{GS} = 10 V; T_{amb} = 25 °C	[1]	-	0.9	A
		V_{GS} = 10 V; T_{amb} = 100 °C	[1]	-	0.6	A
I_{DM}	peak drain current	T_{amb} = 25 °C; single pulse; t_p ≤ 10 µs		-	5.1	A
P_{tot}	total power dissipation	T_{amb} = 25 °C	[2]	-	800	mW
			[1]	-	1700	mW
		T_{sp} = 25 °C		-	6200	mW
T_j	junction temperature			-55	150	°C

Symbol	Parameter	Conditions		Min	Max	Unit
T_{amb}	ambient temperature			-55	150	°C
T_{stg}	storage temperature			-65	150	°C
Source-drain diode						
I_S	source current	T_{amb} = 25 °C	[1]	-	1.6	A

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm^2.

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

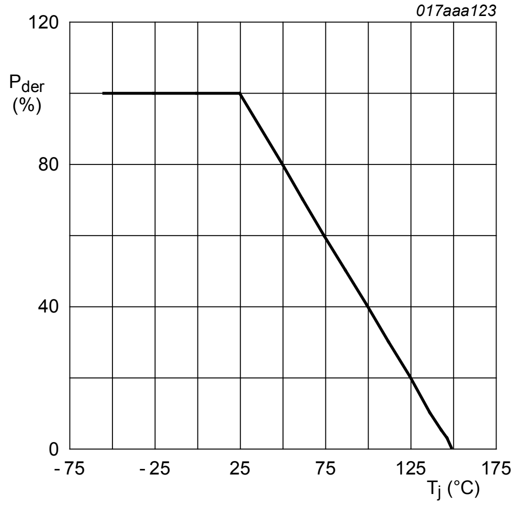


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25°C)}} \times 100\ \%$$

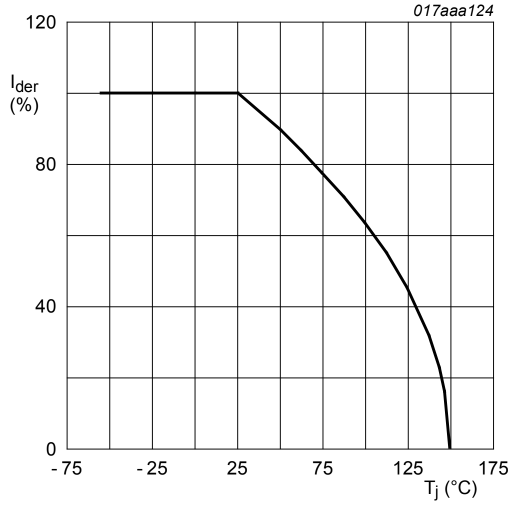
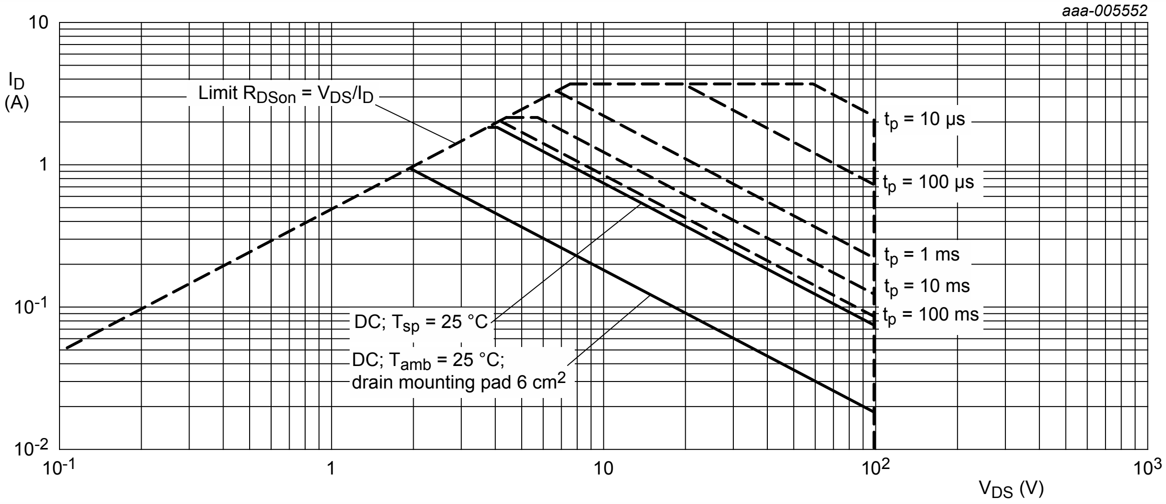


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25°C)}} \times 100\ \%$$



I_{DM} = single pulse

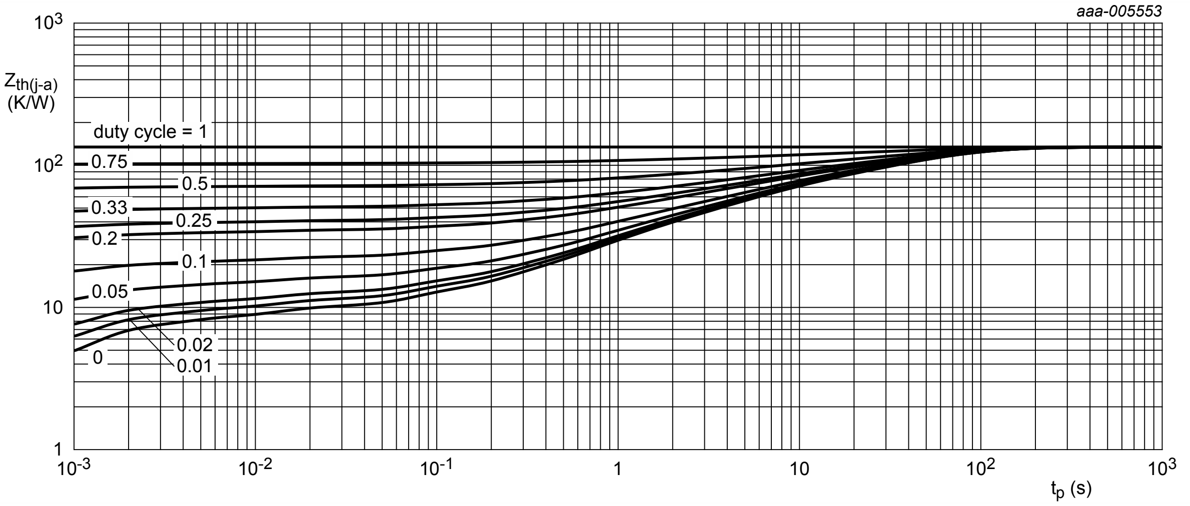
Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

6. Thermal characteristics

Table 6. Thermal characteristics

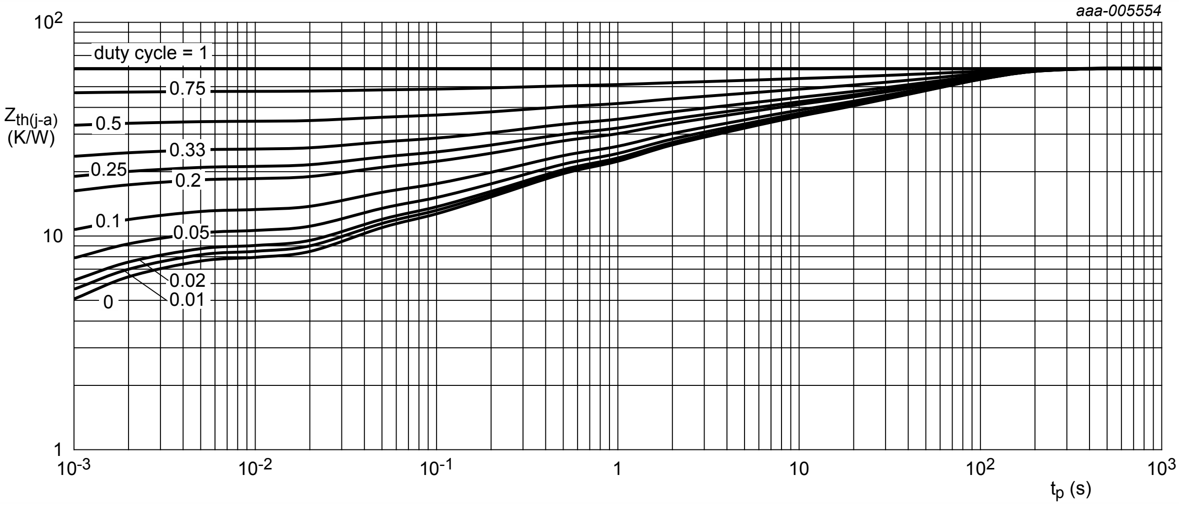
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	135	155	K/W
			[2]	-	60	70	K/W
		in free air; t ≤ 5 s	[2]	-	32	37	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	15	20	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm^2.



FR4 PCB, standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 6 cm^2

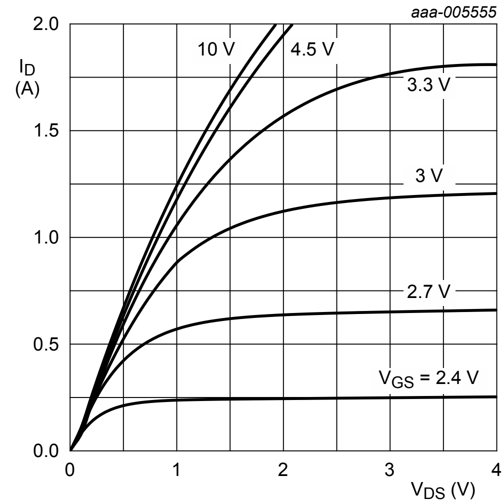
Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

7. Characteristics

Table 7. Characteristics

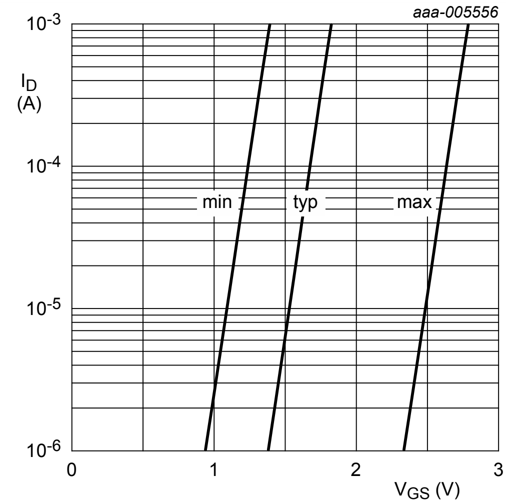
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C		100	-	-	V
V_{GSth}	gate-source threshold voltage	I_D = 250 µA; V_{DS} = V_{GS}; T_j = 25 °C		1.3	1.7	2.5	V
I_{DSS}	drain leakage current	V_{DS} = 100 V; V_{GS} = 0 V; T_j = 25 °C		-	-	1	µA
I_{GSS}	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C		-	-	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C		-	-	-100	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 0.8 A; T_j = 25 °C		-	760	950	mΩ
		V_{GS} = 10 V; I_D = 0.8 A; T_j = 150 °C		-	1.7	2.1	Ω
		V_{GS} = 4.5 V; I_D = 0.8 A; T_j = 25 °C		-	0.8	1	Ω
g_{fs}	forward transconductance	V_{DS} = 10 V; I_D = 0.8 A; T_j = 25 °C		-	1.6	-	S
Dynamic characteristics							
$Q_{G(tot)}$	total gate charge	V_{DS} = 80 V; I_D = 0.8 A; V_{GS} = 10 V; T_j = 25 °C		-	2.4	3	nC
Q_{GS}	gate-source charge			-	0.3	-	nC
Q_{GD}	gate-drain charge			-	0.6	-	nC
C_{iss}	input capacitance	V_{DS} = 80 V; f = 1 MHz; V_{GS} = 0 V; T_j = 25 °C		-	108	160	pF
C_{oss}	output capacitance			-	24	-	pF

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
C_{rss}	reverse transfer capacitance			-	18	-	pF
$t_{d(on)}$	turn-on delay time	V_{DS} = 50 V; I_D = 0.8 A; V_{GS} = 10 V; $R_{G(ext)}$ = 6 Ω; T_j = 25 °C		-	3	-	ns
t_r	rise time			-	3	-	ns
$t_{d(off)}$	turn-off delay time			-	8	-	ns
t_f	fall time			-	3	-	ns
Source-drain diode							
V_{SD}	source-drain voltage	I_S = 0.8 A; V_{GS} = 0 V; T_j = 25 °C		-	0.9	1.2	V



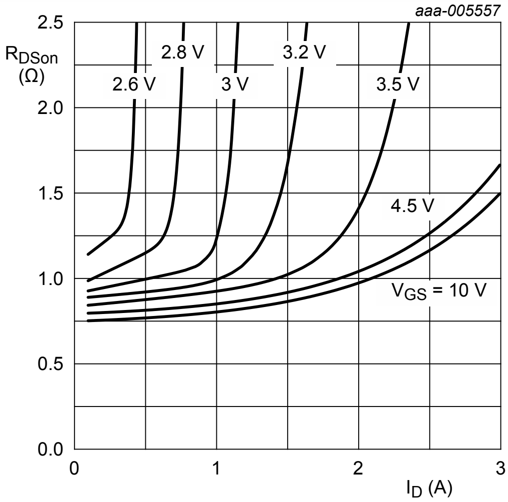
T_j = 25 °C

Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values



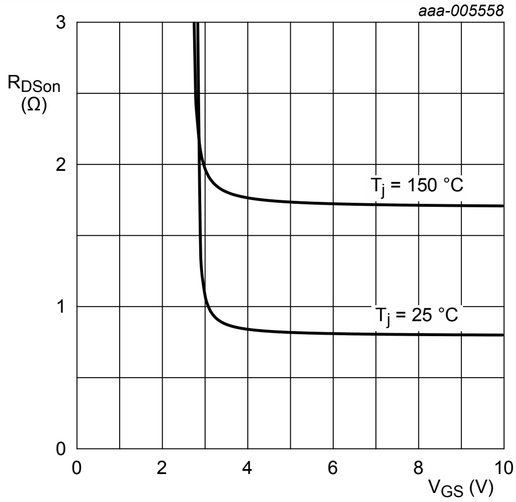
T_j = 25 °C; V_{DS} = 5 V

Fig. 7. Subthreshold drain current as a function of gate-source voltage



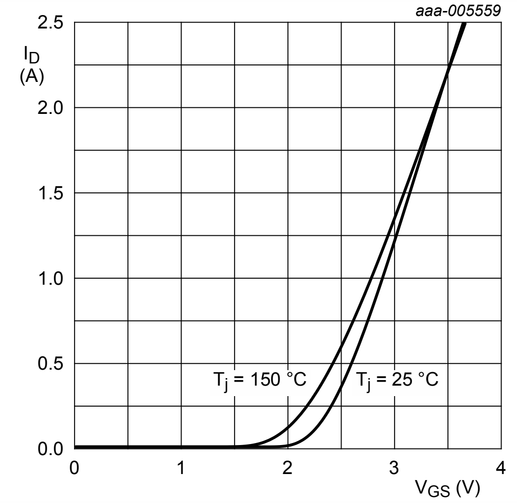
T_j = 25 °C

Fig. 8. Drain-source on-state resistance as a function of drain current; typical values



I_D = 0.8 A

Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values



$V_{DS} > I_D \times R_{DSon}$

Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

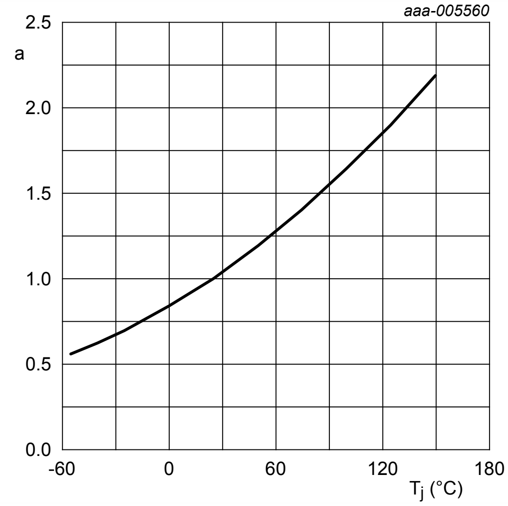
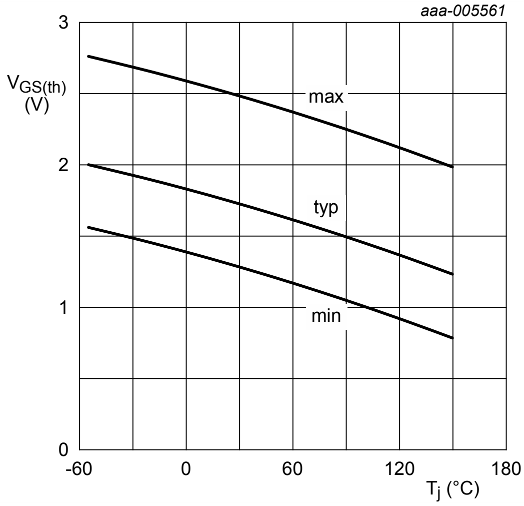


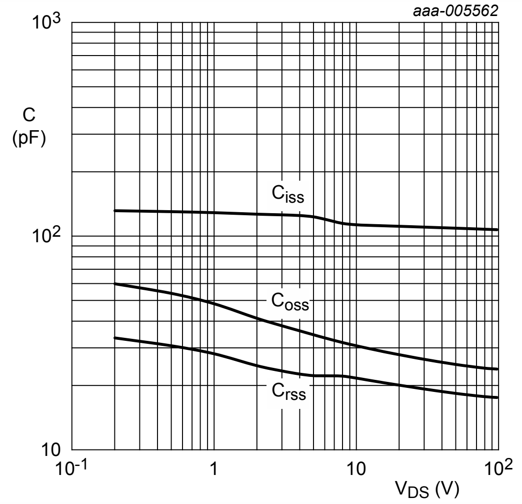
Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$



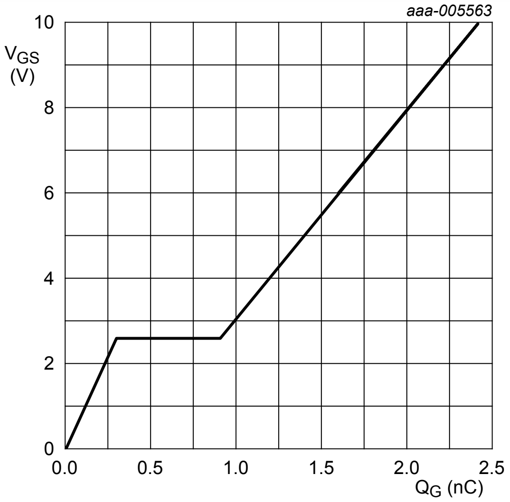
$I_D = 0.25$ mA; $V_{DS} = V_{GS}$

Fig. 12. Gate-source threshold voltage as a function of junction temperature



f = 1 MHz; $V_{GS} = 0$ V

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



I_D = 0.8 A; V_{DS} = 80 V; T_{amb} = 25 °C

Fig. 14. Gate-source voltage as a function of gate charge; typical values

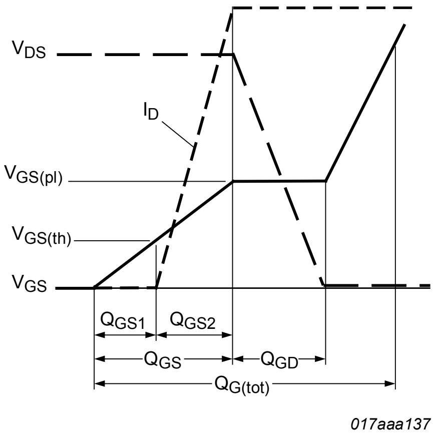
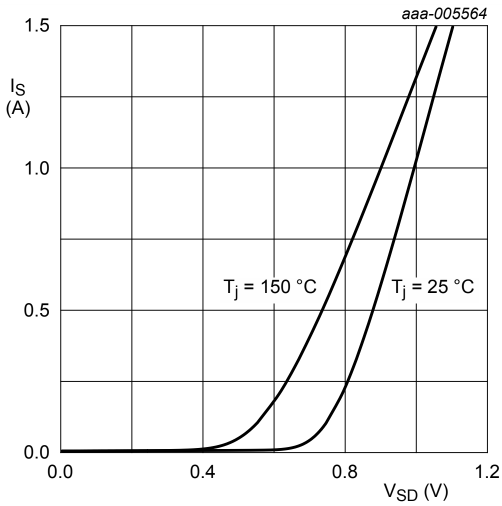


Fig. 15. Gate charge waveform definitions



V_{GS} = 0 V

Fig. 16. Source current as a function of source-drain voltage; typical values

8. Test information

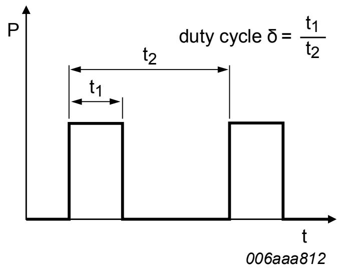


Fig. 17. Duty cycle definition

9. Package outline

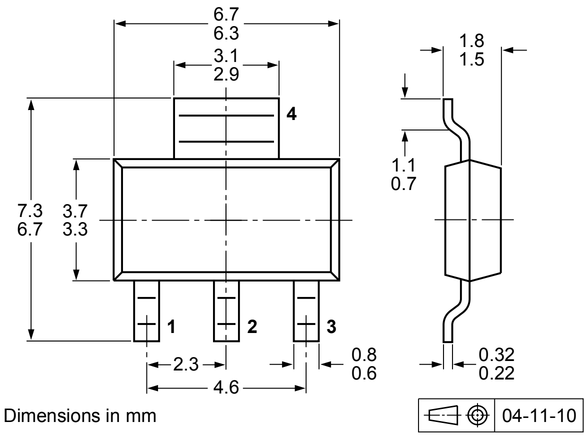


Fig. 18. Package outline SC-73 (SOT223)

10. Soldering

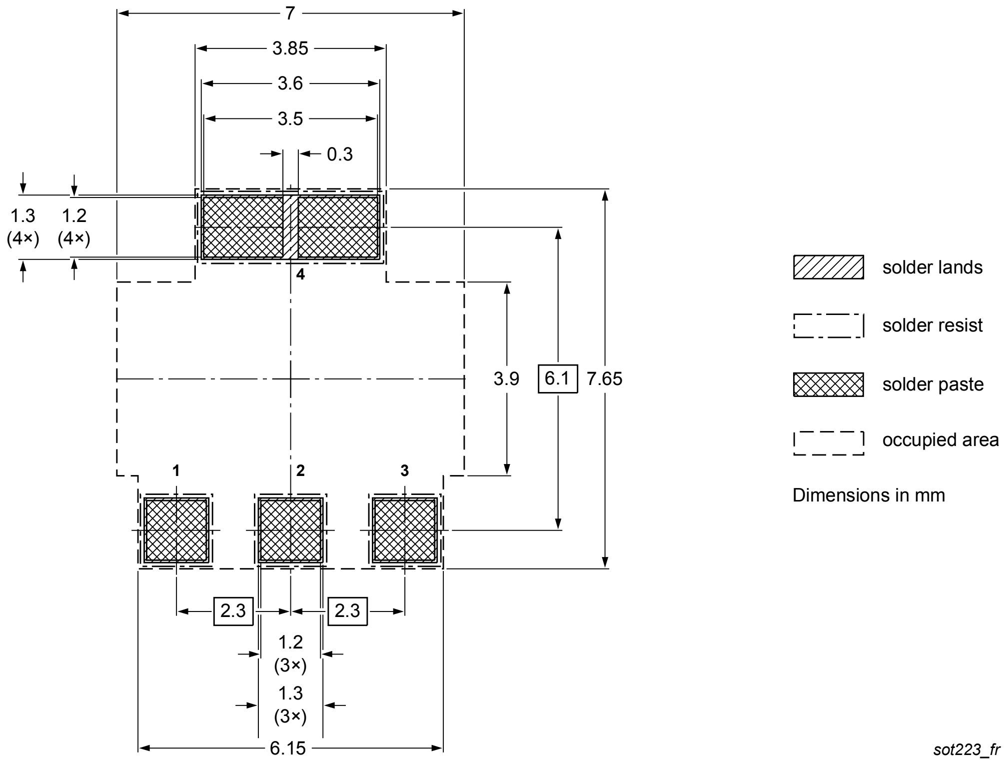


Fig. 19. Reflow soldering footprint for SC-73 (SOT223)

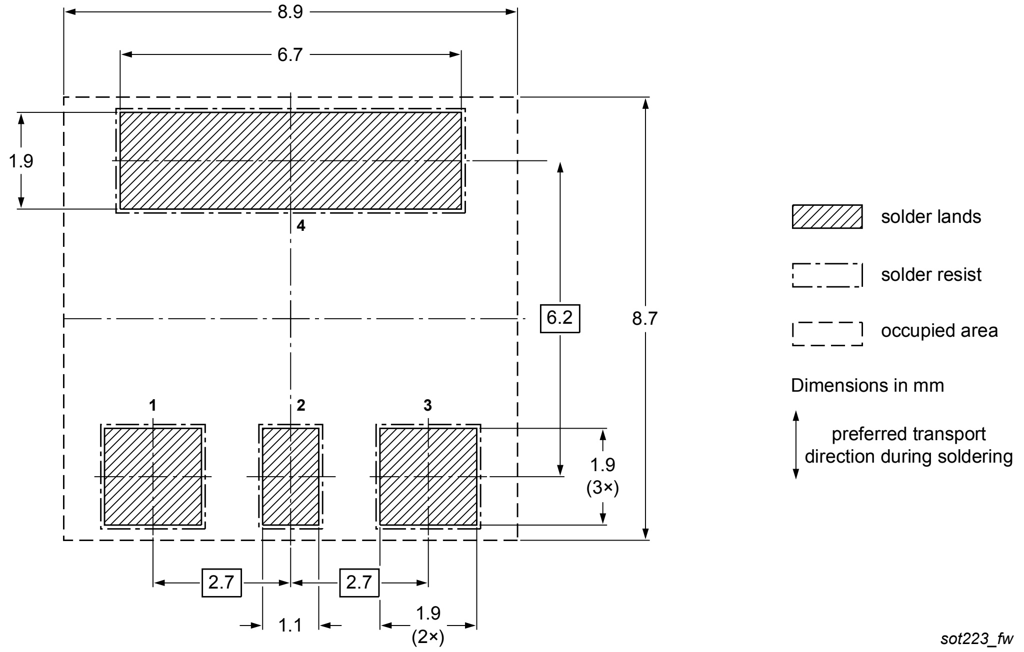


Fig. 20. Wave soldering footprint for SC-73 (SOT223)

11. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMT760EN v.1	20121025	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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